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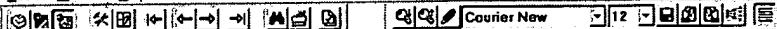
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US-PAT-NO: 5793126

DOCUMENT-IDENTIFIER: US 5793126 A

TITLE: Power control chip with circuitry that isolates switching elements and bond wires for testing

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TITLE - TI:

Power control chip with circuitry that isolates switching elements and bond wires for testing

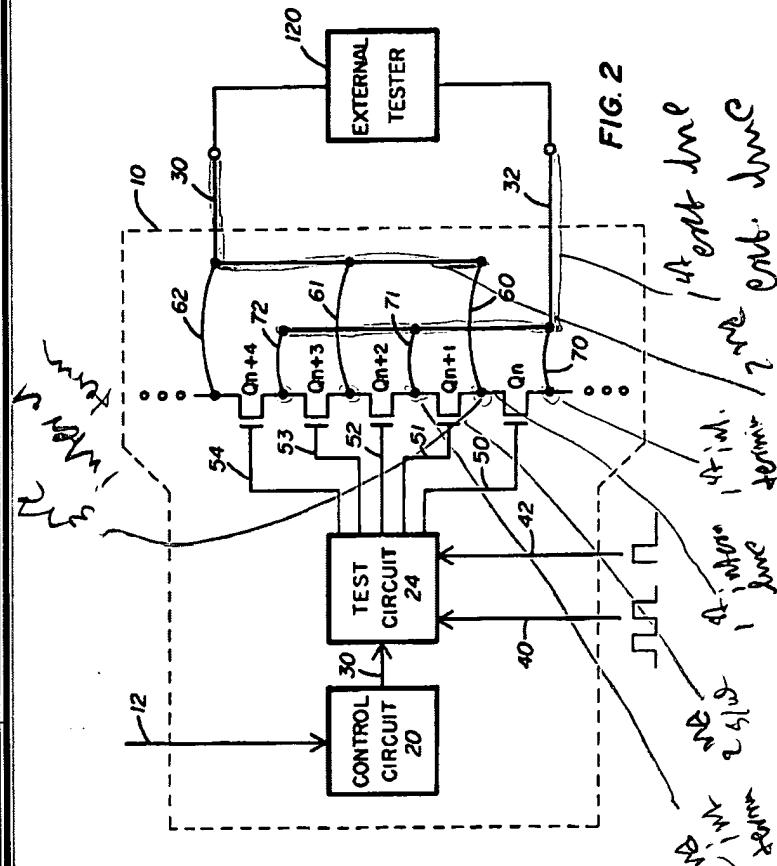
	Document ID	Kind Codes	Source	Issue Date	Pages	Dev.
2	US 20020030088		US-PGPUB	20020314	14	Dev.
3	US 6334566 B1		USPAT	20020101	14	Dev.
4	US 6299049 B1		USPAT	20011009	15	Dev.
5	US 6230569 B1		USPAT	20010515	9	Use
6	US 5994910 A		USPAT	19991130	7	App.
7	US 5894981 A		USPAT	19990420	14	Int.
8	US 5793126 A		USPAT	19980811	17	Power

U.S. Patent

Aug. 11, 1998

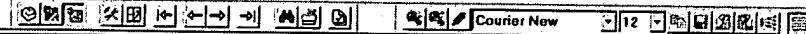
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6 and 8. In other words, as shown in FIG. 21(a) the eleventh embodiment has a plurality of contact terminals 47 arrayed in the mold 80 of the silicon wafer, as described later with reference to FIG. 17(b), to correspond to the electrodes 3 of the device under test, tin plating 204 formed on the surface of the electrodes 200 integrated with each contact terminal, and gold plating 205 formed on the electrode 69 of the polyimide film 65 forming the lead out wire 48 are subjected to heat expansion, connected by forming a lead alloy and a multilayer film 44 comprising the contact terminals 47 formed by an integration of the polyimide film 65 and the electrode 200.

DEPR:

The contact terminal 47 of this embodiment is further capable of easily adapting to semiconductor devices with an electrode pitch narrower than 0.1 mm, to a range of 10 to 20 μm . More specifically, one side of the bottom of the contact terminal 47 can easily be formed to a size of 5 μm . In terms of the multilayer film, the height of the contact terminal 47 can be achieved at a precision within $\pm 2 \mu\text{m}$ during forming, and, as a result, even when utilizing the clamping member (clamp plate) 43 on the area 44a arrayed with a plurality of contact terminals 47 to enclose the cushioning layer 46 and cause a projection to eliminate slack in the multilayer film

[Details](#) [Text](#) [Image](#) KWC

U	1	Document ID	Issue Date	Pages	Title
1	<input checked="" type="checkbox"/>	US 20010009376	20010221	21	Probe arrangement assembly, probe arrangement
2	<input type="checkbox"/>	US 6305230	20011023	34	Connector and probing system
3	<input type="checkbox"/>	US 5593335	19970114	95	Method of manufacturing an A
4	<input type="checkbox"/>	US 5380681	19950110	12	Three-dimensional multichip fabricating A

[Details](#) [Text](#) [Image](#)

Kasukabe et al.

(45) Date of Patent: Oct. 23, 2001

(54) CONNECTOR AND PROBING SYSTEM

5-243344 9/1993 (JP).
7-283280 10/1995 (JP).
8-033242 3/1996 (JP).
8-220138 8/1996 (JP).

OTHER PUBLICATIONS

Leslie et al., "Membrane Probe Card Technology", 1996 IEEE International Test Conference, Paper 30.1, pp. 601-607.

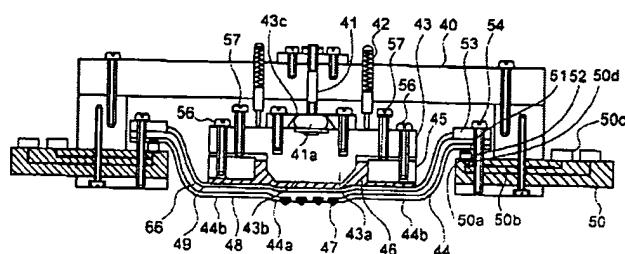
* cited by examiner

Primary Examiner—Max Nocci
(74) Attorney, Agent, or Firm—Astonelli, Terry, Stout & Kraus, LLP

(57) ABSTRACT

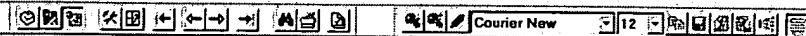
A connection device and test system is capable of stable, low load damage-free probing of devices under test, which have many pins with a narrow pitch. Furthermore in order to achieve high speed exchange of electrical signals or so-called high frequency electrical signals, a support member is provided for supporting the connection device, a plurality of pointed contact terminals are arrayed in an area of the probing site, a multilayer film is provided having a plurality of lead out wires electrically connected to the contact terminals and a ground layer enclosing an insulation layer, and a frame is clamped on the rear side of the multilayer film. A clamping member is provided on the frame to make the multilayer film project out to eliminate slack in the multilayer film, a contact pressure means is provided for making the tips of the contact terminals contact each of the electrodes with predetermined contact pressure from the support member to the clamping member, and a compliance mechanism is provided so that the contact terminal group of the tip surface is arrayed in parallel with the electrode group terminal surface, so that the tips of the contact terminals contact the surface of the electrodes with an equal pressure.

14 Claims, 18 Drawing Sheets



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DOCUMENT-IDENTIFIER: US 5469733 A

TITLE: Cantilever for atomic force microscope and method of manufacturing the cantilever

ABSTRACT:

A cantilever for an atomic force microscope includes a probe and a cantilever body supporting the probe, the probe deflecting in response to an atomic force between said probe and a sample, at least the surface of the probe including one of a resist film and a sputtered film. One method of manufacturing the cantilever includes selectively etching the surface of a silicon substrate to form an etch pit, forming a resist film in at least the etch pit, forming a nitride film on the resist film, forming a glass base plate on the nitride film in a predetermined area not including the etch pit, and removing the silicon substrate. An atomic force microscope is also provided in which the cantilever is used to measure an atomic force between a sample and the probe having a desired film on a surface. A sample surface evaluating method is further provided by which the adhesion between the desired film or substance and the sample surface can be evaluated quantitatively from the measured atomic force without damaging the sample surface.

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Document ID	Kind Codes	Source	Issue Date	Pages
1 US 5469733 A	USPAT	19951128	26	Canti

United States Patent [19]

Yasue et al.

(11) Patent Number: 5,469,733

(43) Date of Patent: Nov. 28, 1995

[54] CANTILEVER FOR ATOMIC FORCE MICROSCOPE AND METHOD OF MANUFACTURING THE CANTILEVER

(75) Inventor: Takeshi Yasue; Tadashi Nishio, both of Ibaraki, Japan

(73) Assignee: Mitsubishi Denki Kabushiki Kaisha, Tokyo, Japan

(21) Appl. No.: 134,169

(22) Filed: Feb. 9, 1994

(30) Foreign Application Priority Data

Feb. 16, 1993 JPN Japan 5-026841

(51) Int. Cl. 4 G01B 5/28; H01J 37/15

(52) U.S. Cl. 73/185; 250/106; 250/307

(36) Field of Search 73/185; 250/106; 250/307, 423 P

(56) References Cited

U.S. PATENT DOCUMENTS

4,998,016	3/1/91	New et al.	250/307
5,021,364	6/1/91	Akamatsu et al.	250/306
5,031,379	9/1/91	Bayer et al.	437/223
5,046,170	8/25/91	Yamada et al.	250/306
5,164,520	11/19/92	Froer et al.	250/307
5,208,571	12/19/93	Yamamoto et al.	250/307
5,217,533	5/19/93	Quate et al.	250/307
5,334,833	8/1/94	Nakayama et al.	250/307

OTHER PUBLICATIONS

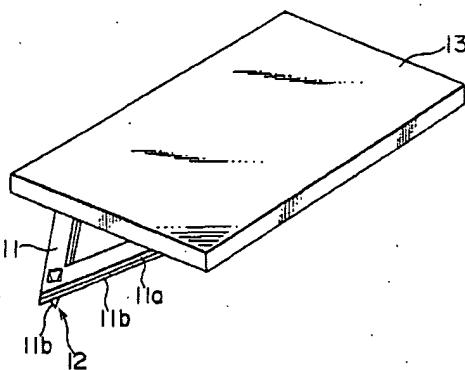
Chalmers et al., "Determination of Three Superlattice Structure by Atomic Force Microscopy", Applied Physics Letters 35, Dec., 1979, pp. 2491-2493.

Primary Examiner—Richard Chilton
Assistant Examiner—George M. Dombrink
Attorney, Agent, or Firm—Leydig, Voit & Mayer

(57) ABSTRACT

A cantilever for an atomic force microscope includes a probe and a cantilever body supporting the probe, the probe deflecting in response to an atomic force between said probe and a sample, at least the surface of the probe including one of a resist film and a sputtered film. One method of manufacturing the cantilever includes selectively etching the surface of a silicon substrate to form an etch pit, forming a resist film in at least the etch pit, forming a nitride film on the resist film, forming a glass base plate on the nitride film in a predetermined area not including the etch pit, and removing the silicon substrate. An atomic force microscope is also provided in which the cantilever is used to measure an atomic force between a sample and the probe having a desired film on a surface. A sample surface evaluating method is further provided by which the adhesion between the desired film or substance and the sample surface can be evaluated quantitatively from the measured atomic force without damaging the sample surface.

9 Claims, 18 Drawing Sheets



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Detailed Description Text - DETX:

The power supply portion of 12 provides voltage at two levels, for example, approximately -7 to -15 volts, for providing stimulating pulse energy storage and -2 to -4 volts for power for digital logic 16. Data detector 12 also provides clock and digital data information to logic 16 which decodes the control information contained within the modulated, alternating magnet field. Such decoded information is used by the logic 16 to control switch 17 which controls the charge stored on the capacitor 20, between electrodes 14 and 15. Logic 16, which is preferably high speed, low current, silicon gate CMOS, also controls switch 18, (which may be a transistor), which controls the stimulating pulse current (which is a discharge of the stored charge between electrodes 14 and 15) which flows between electrodes 14 and 15.. Logic 16 also controls current amplitude buffer 19. This controls the amount of current allowed to flow in each stimulating pulse.

	Document ID	Kind Codes	Source	Issue Date	Pages	
115	US 5193540 A		USPAT	19930316	16	Str
116	US 5128737 A		USPAT	19920707	43	Sem
117	US 5119162 A		USPAT	19920602	24	Int
118	US 5099309 A		USPAT	19920324	12	Thr
119	US 5074629 A		USPAT	19911224	42	Int
120	US 4966646 A		USPAT	19901030	44	Met
121	US 4943032 A		USPAT	19900724	59	Int

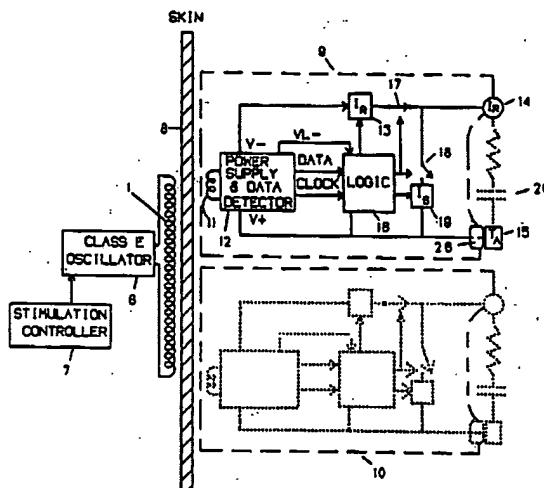


FIG. 2

US-PAT-NO: 5358514

DOCUMENT-IDENTIFIER: US 5358514 A

TITLE: Implantable microdevice with self-attaching electrodes

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Detailed Description Text - DETX:

The power supply portion of 12 provides the operating and stimulating voltages for the microdevice, with the energy being derived from the signal received through the coil 11 as coupled from the coil 40. The operating voltage may be at two levels, for example, approximately -7 to -15 volts, for providing stimulating pulse energy storage; and -2 to -4 volts for providing operating power for digital logic 16. Data detector 12 also provides clock and digital data information to logic 16 which decodes the control information contained within the modulated, alternating magnet field. Such decoded information is used by the logic 16 to control switch 17 which controls the charge stored on the capacitor 20, connected between electrodes 14 and 15. Capacitor 20 is located inside the hermetically sealed tube that comprises the housing of the microdevice 9. In some embodiments, the capacitor 20 may actually be found outside of the housing using the electrodes 14 and 15 but

Details Text Image HTML KWC

U.S. Patent

Oct. 25, 1994

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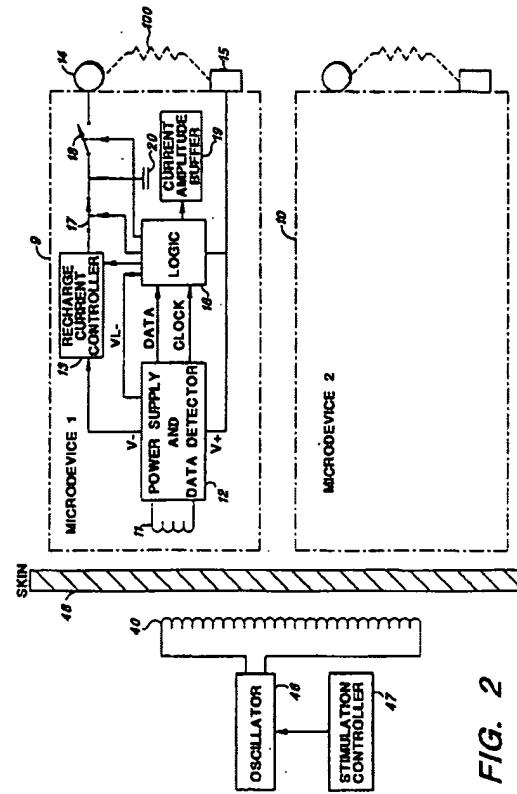


FIG. 2

Document ID	Kind Codes	Source	Issue Date	Pages	Imp.
104	US 5358514 A	USPAT	19941025	17	
105	US 5355102 A	USPAT	19941011	16	HDI
106	US 5315130 A	USPAT	19940524	39	Ver.
107	US 5314458 A	USPAT	19940524	19	Sin.
108	US 5280192 A	USPAT	19940118	14	Thr.
109	US 5276455 A	USPAT	19940104	42	Pac.
110	US 5274350 A	USPAT	19931228	6	Shu.